

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) Professional
PART NUMBER: SLP-WB89A-51
MANUFACTURER: SANYO
REMARK: TA= - 40 degree C

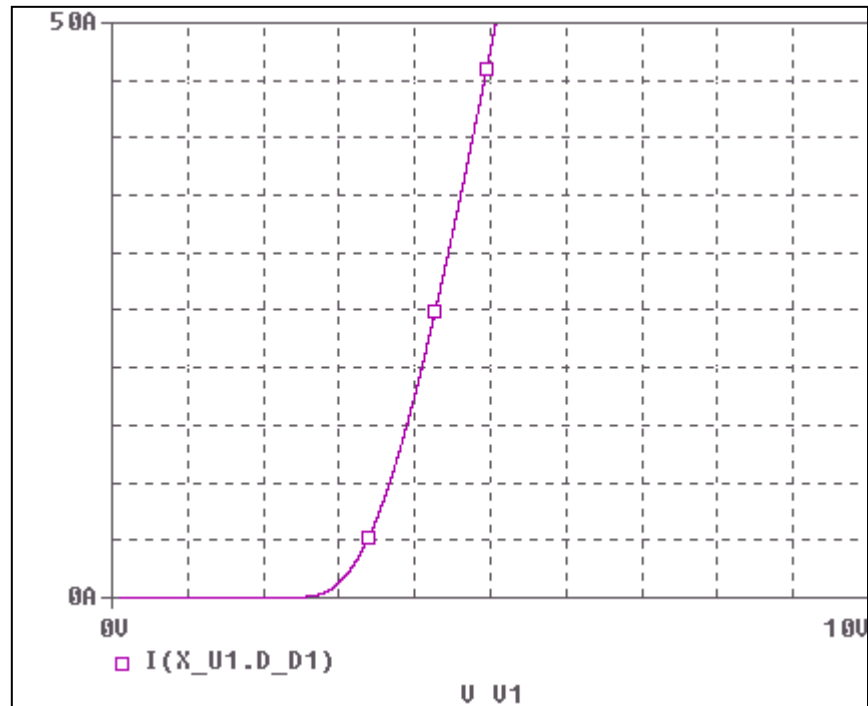


Bee Technologies Inc.

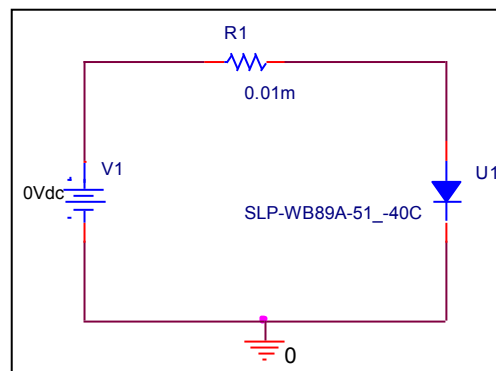
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

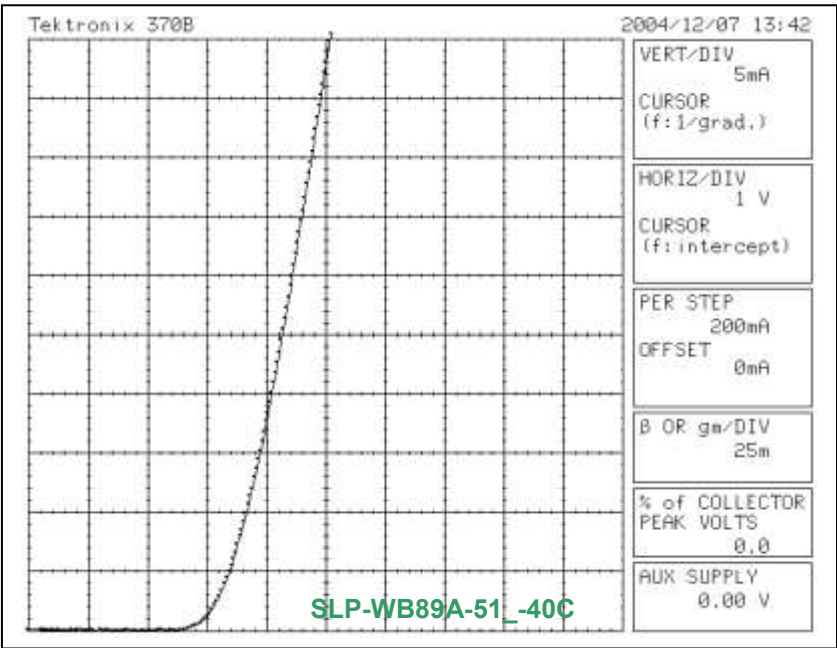


Evaluation Circuit



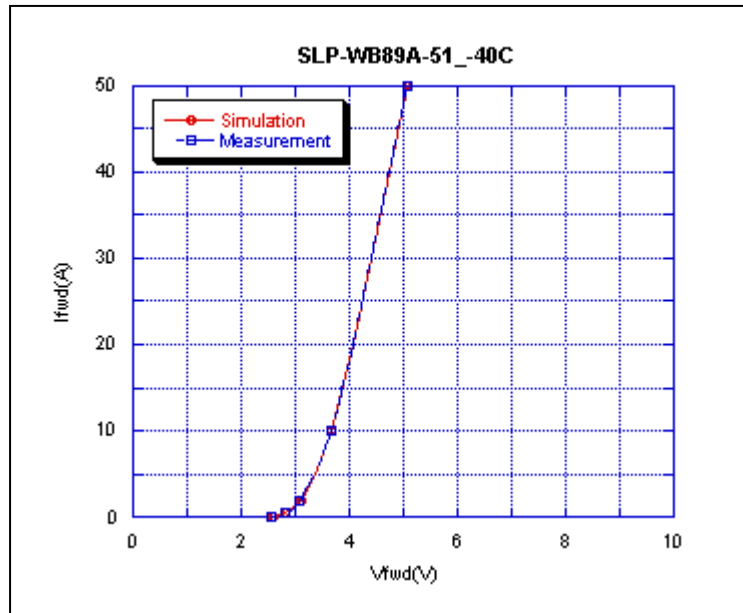
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

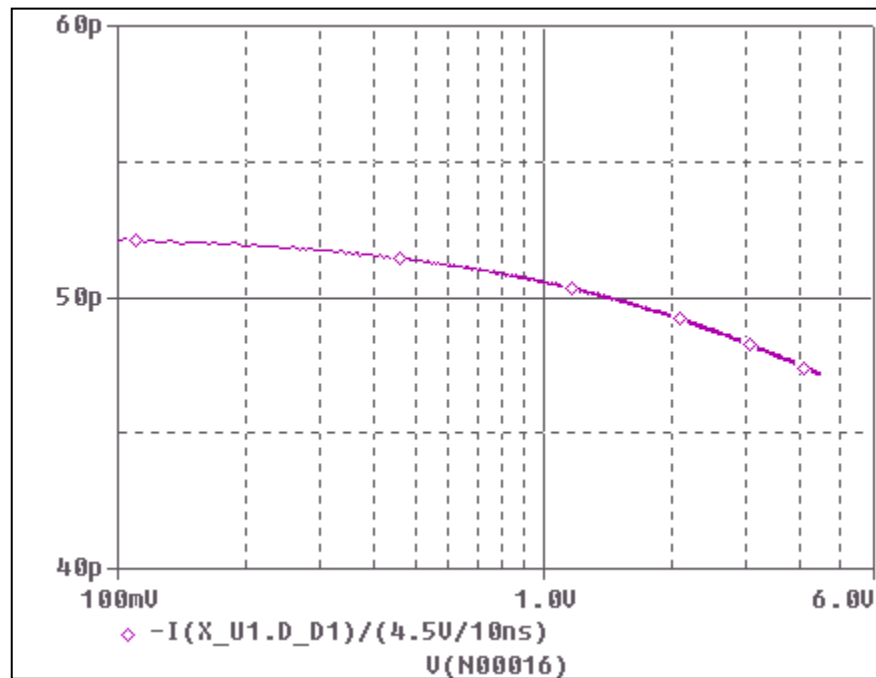


Simulation Result

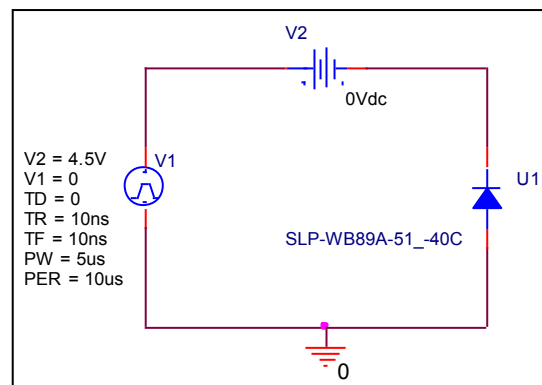
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.1	2.57	2.586	0.62256
0.2	2.68	2.682	0.07462
0.5	2.83	2.821	0.31802
1	2.97	2.943	0.90909
2	3.08	3.095	0.48701
5	3.38	3.372	0.23668
10	3.66	3.667	0.19125
20	4.09	4.092	0.04889
50	5.07	5.068	0.03944

Capacitance Characteristic

Circuit Simulation Result

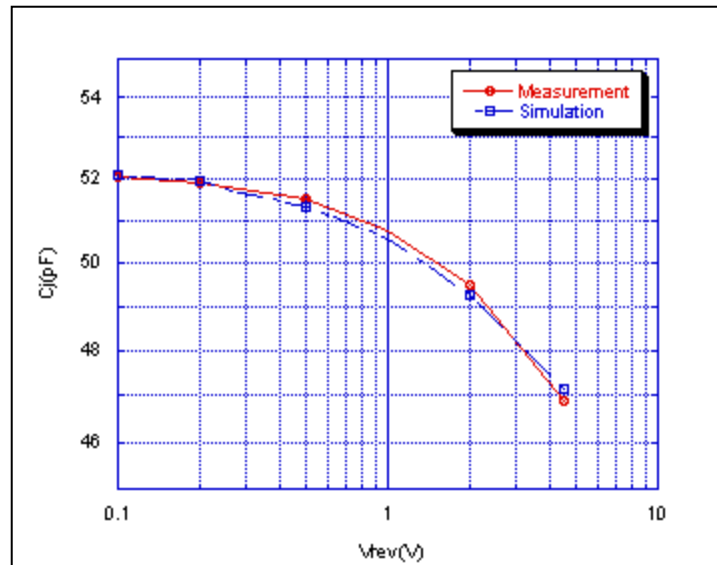


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

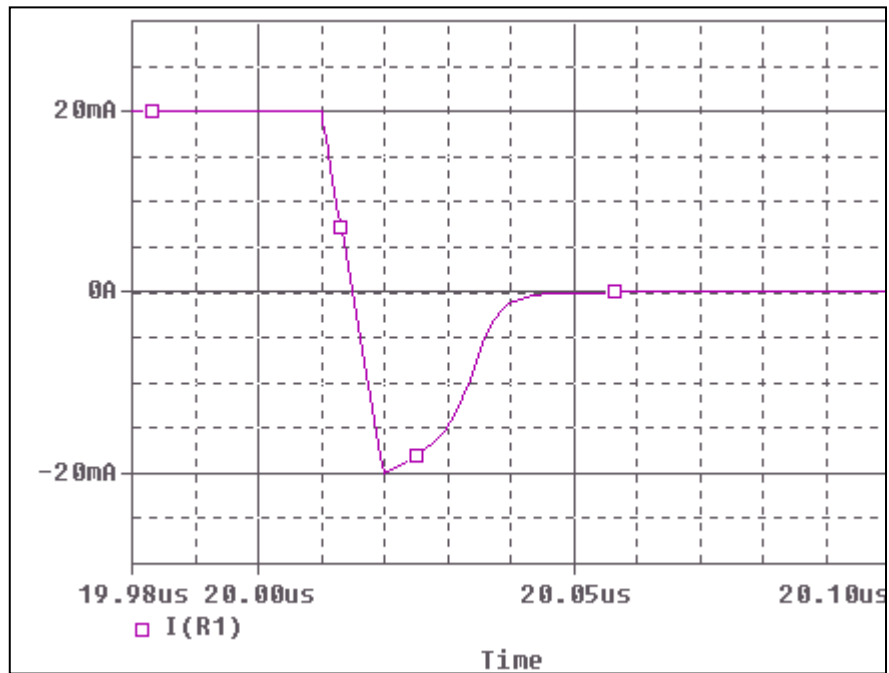


Simulation Result

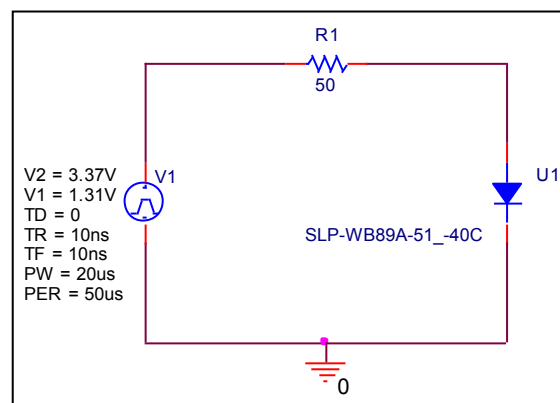
V_{rev} (V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	52.14	52.14	0
0.1	52.05	52.11	0.1152
0.2	51.9	51.93	0.0578
0.5	51.5	51.33	0.3300
1	50.75	50.56	0.3743
2	49.5	49.28	0.4444
4.5	46.9	47.15	0.5330

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

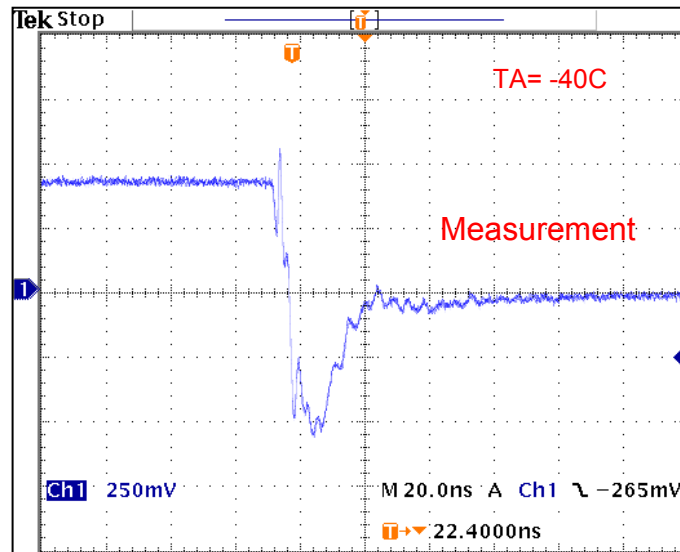


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
trj	7.2	ns	7.29	ns	1.25
trb	16	ns	15.93	ns	-0.4375

Reverse Recovery Characteristic

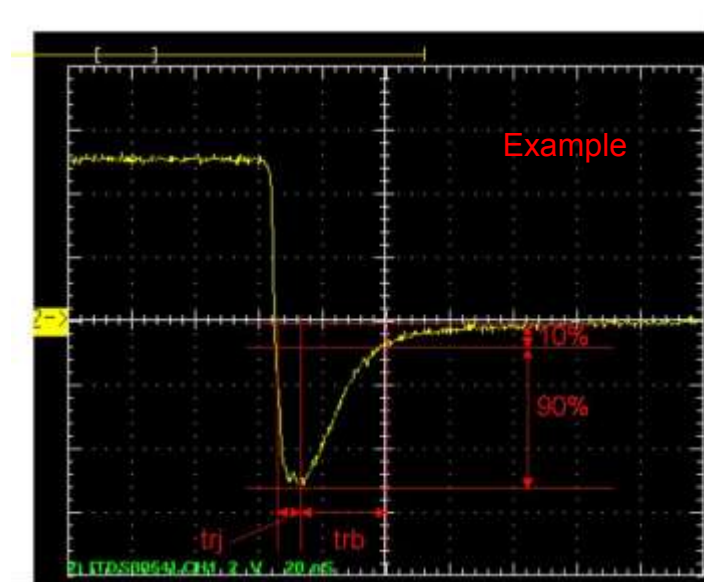
Reference



$T_{rj} = 7.2(\text{ns})$

$T_{rb} = 16(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}